TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK2467

High-Power Amplifier Application

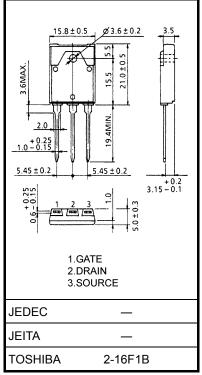
- High breakdown voltage: VDSS = 180 V
- High forward transfer admittance: $|Y_{fs}| = 4.0 \text{ S}$ (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V _{DSS}	180	V
Gate-source voltage	V _{GSS}	±20	V
Drain current (Note 1)	۱ _D	9	А
Drain power dissipation (Tc = 25°C)	PD	80	W
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55 to 150	°C

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).



Weight: 5.8 g (typ.)

Electrical Characteristics (Ta = 25°C)

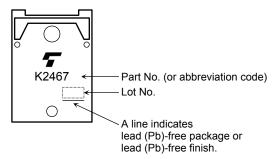
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} = 180 V, V _{GS} = 0	—	_	1.0	mA
Gate leakage current	I _{GSS}	V _{DS} = 0, V _{GS} = ±20 V	_	_	±0.5	μA
Drain-source breakdown voltage	V (BR) DSS	I_{D} = 10 mA, V_{GS} = 0	180	—		V
Drain-source saturation voltage	V _{DS (ON)}	V _{GS} = 10 V, I _D = 6 A		2.5	5.0	V
Gate-source cut-off voltage (Note 3)	V _{GS (OFF)}	V _{DS} = 10 V, I _D = 0.1 A	1.4	—	2.8	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3 A	_	4.0	—	S
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz	_	700	_	pF
Output capacitance	C _{oss}	V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz	—	150	—	pF
Reverse capacitance	C _{rss}	V_{DS} = 30 V, V_{GS} = 0, f = 1 MHz	_	90	_	pF

Note 3: V_{GS (OFF)} classification Y: 1.4 to 2.8

This transistor is an electrostatic-sensitive device. Plese handle with caution.

TOSHIBA

Marking



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20070701-EN

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